

IN THE CLAIMS

Please amend Claim 1 and Claim 3 as follows:

- C2
1. (Currently Amended) A method of nickel silicidation comprising:
- forming a processed substrate including partially fabricated integrated circuit components and a silicon substrate;
 - incorporating nitrogen into said processed substrate and annealing the processed substrate;
 - depositing nickel onto said processed substrate after incorporating nitrogen into said processed substrate; and
 - annealing said processed substrate so as to form nickel mono-silicide.

- C3
3. (Currently Amended) The method as claimed in claim 2, wherein said forming a processed substrate comprises:
- forming dielectric regions in said silicon substrate that electrically isolate neighboring integrated circuit devices;
 - doping a portion of said silicon substrate with an n-type and a p-type doping to form said source/drain structures;
 - depositing a gate dielectric material and a polycrystalline silicon gate material onto said silicon substrate and selectively etching; and
 - depositing a dielectric material onto said silicon substrate and selectively etching to form dielectric spacers.